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November 2013

FQL40N50

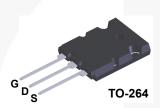
N-Channel QFET® MOSFET 500 V, 40 A, 110 mΩ

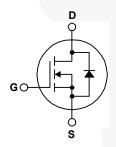
Description

This N-Channel enhancement mode power MOSFET is • 40 A, 500 V, $R_{DS(on)}$ = 110 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 155 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 95 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 20 A$





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQL40N50	Unit
V _{DSS}	Drain-Source Voltage		500	V
I _D	Drain Current - Continuous (T _C = 25°C)		40	А
	- Continuous (T _C = 100°C)		25	А
I _{DM}	Drain Current - Pulsed	Note 1)	160	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	Note 2)	1780	mJ
I _{AR}	Avalanche Current	Note 1)	40	А
E _{AR}	Repetitive Avalanche Energy	Note 1)	46	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3		(Note 3) 4.5	
P_{D}	Power Dissipation (T _C = 25°C)		460	W
	- Derate above 25°C		3.7	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _I	Maximum lead temperature for soldering,		300	°C
· L	1/8" from case for 5 seconds.		300	

Thermal Characteristics

Symbol	Parameter	FQL40N50	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.27	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	30	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQL40N50	FQL40N50	TO-264	Tube	N/A	N/A	25 units

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		0.48		V/°C
I _{DSS}		V _{DS} = 500 V, V _{GS} = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 400 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 20 A		0.085	0.11	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 50 \text{ V}, I_{D} = 20 \text{ A}$		29		S
Dynami	ic Characteristics				,	
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	\	5800	7500	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		880	1150	pF
C _{rss}	Reverse Transfer Capacitance			95	120	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 250 \text{ V}, I_{D} = 40 \text{ A},$		140	290	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		440	890	ns
t _{d(off)}	Turn-Off Delay Time	- · · · · · · · · · · · · · · · · · · ·		350	700	ns
t _f	Turn-Off Fall Time	(Note 4)		250	500	ns
Q_g	Total Gate Charge	V _{DS} = 400 V, I _D = 40 A,		155	200	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		37		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		78		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				40	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				160	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 40 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 40 A,		520		ns
Q _{rr}	Payersa Pacovery Charge	dl _F / dt = 100 A/ μ s		8.0	//	μС

^{1.} Repetitive rating : pulse-width limited by maximum junction temperature.

^{2.} L = 2.0 mH, I_{AS} = 40 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} \leq 40 A, di/dt \leq 200 A/ μ s , V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

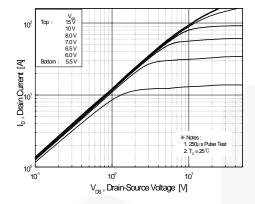


Figure 1. On-Region Characteristics

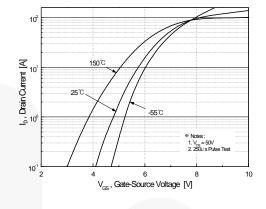


Figure 2. Transfer Characteristics

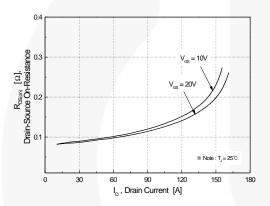


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

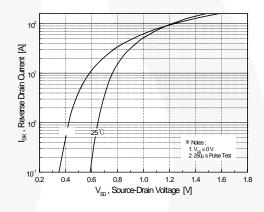


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

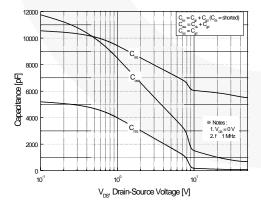


Figure 5. Capacitance Characteristics

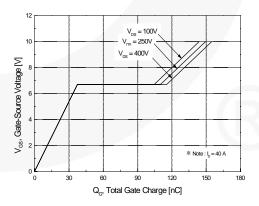


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

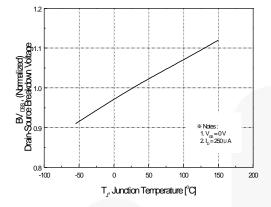


Figure 7. Breakdown Voltage Variation vs. Temperature

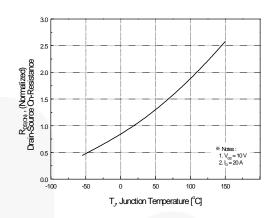


Figure 8. On-Resistance Variation vs. Temperature

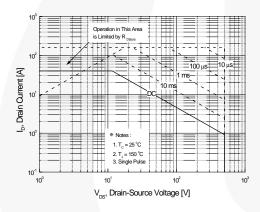


Figure 9. Maximum Safe Operating Area

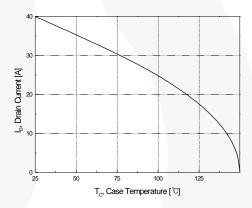


Figure 10. Maximum Drain Current vs. Case Temperature

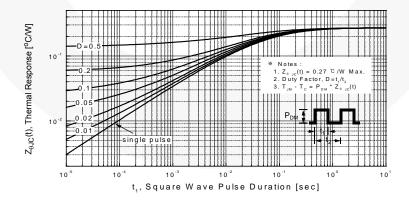


Figure 11. Transient Thermal Response Curve

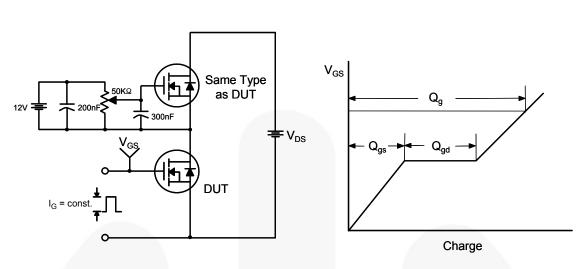


Figure 12. Gate Charge Test Circuit & Waveform

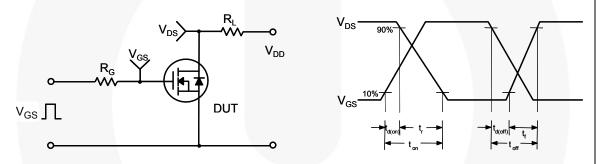


Figure 13. Resistive Switching Test Circuit & Waveforms

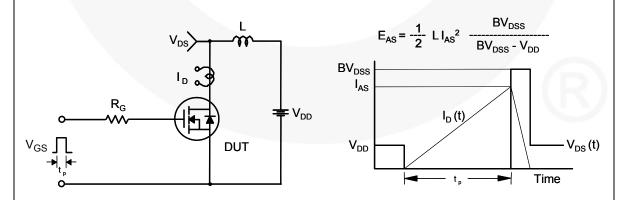
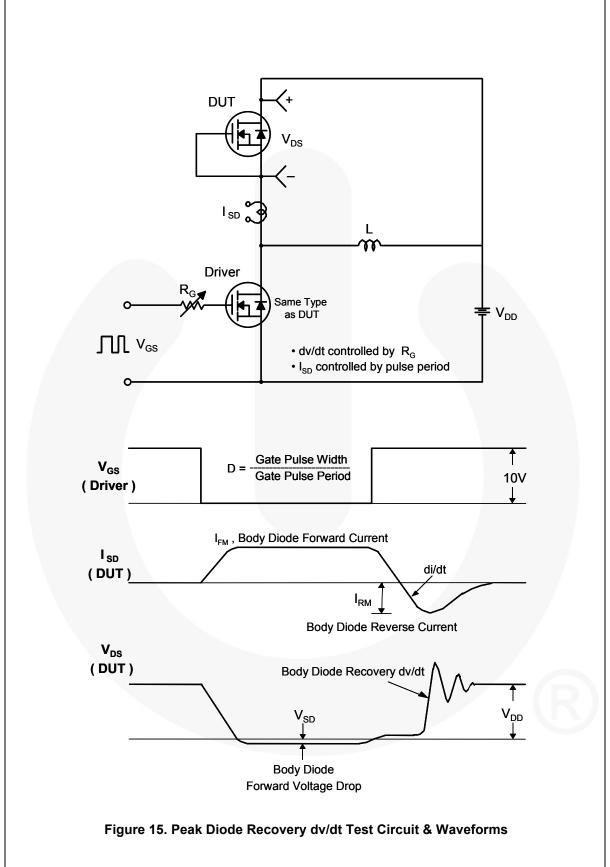
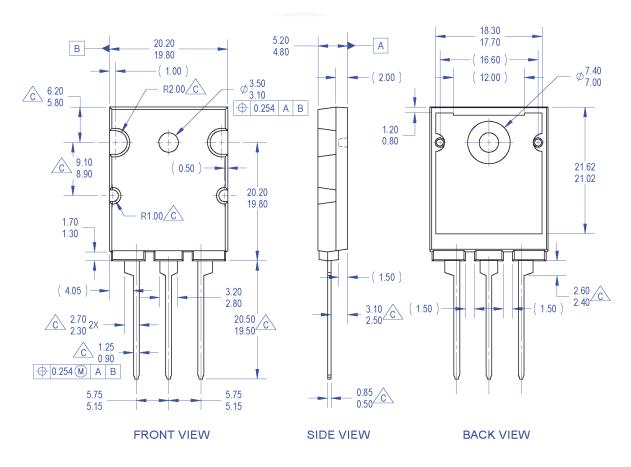
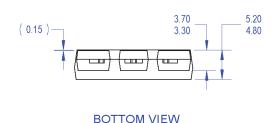


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions





NOTES:

- A. PACKAGE REFERENCE: JEDEC TO264 VARIATION AA
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- OUT OF JEDEC STANDARD VALUE.
 DIMENSION AND TOLERANCE AS PER ASME
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- G. DRAWING FILE NAME: TO264A03REV1

Figure 16. TO264, Molded, 3-Lead, Jedec Variation AA

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